

**Amendments to the Specification:**

Please replace the paragraph, beginning at page 5, line 9, with the following rewritten paragraph:

The initial contact force of the tips may be tuned by adjusting the angle of the see-saw ~~sew-saw~~-interconnect with respect to the approach direction of the test contacts. This may be utilized to improve the tips' scribing on the test pads.

Please replace the paragraph, beginning at page 16, line 9, with the following rewritten paragraph:

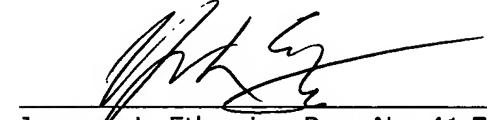
The graph of **Fig. 10** shows two trial curves for transmission resistance over current flow for an exemplary interconnect stage according to **Figs. 1-3, 4B, 5A**. As can be seen in curve of the torsion trial 1, the transmission resistance increases substantially at about 1.5A current flow and about 0.04 mOhms. This indicates a temperature rise to a level where the bonding strength of the adhesive decreases below the shear stress in the delamination origins **204**. Consequently, delamination is initiated resulting ~~relusting~~ in a reduced displacement of the resilient features **215, 216** and a corresponding decrease of the opposing spring force provided by the resilient features **215, 216**. This in turn reduces the contact pressure and well known scribing between the contact tip segments **311, 312, 331, 332** and their corresponding contacts **TC, 102** such that the contact resistance in the interface between the contact tip segments **311, 312, 331, 332** and their corresponding contacts **TC, 102** gradually increases.

Please replace the paragraph, beginning at page 17, line 6, with the following rewritten paragraph:

The block **1002** represents the fabrication of the carrier grid **21** together with the circumferential support frame **4** and eventual stiffening structures **401**. A dielectric thin film **2** deposited on a substrate is patterned and shaped. The dielectric thin film **2** is preferably made of a polymer such as polyimide. The substrate may be stainless steel or any other suitable material as may be appreciated by anyone skilled in the art. The carrier grid **21** is preferably a dielectric laminate that is laminated to the conductive layer and consecutively released by removing the underneath substrate except the eventually stiffening structures **401**, which may be altered in thickness by a separate material removal process.

Respectfully submitted,

RatnerPrestia



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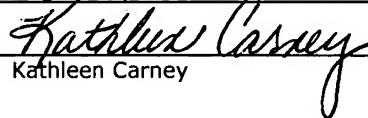
Dated: August 30, 2004

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The Commissioner for Patents is hereby authorized to charge payment to Deposit Account No. **18-0350** of any fees associated with this communication.

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August 30, 2004



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Kathleen Carney